

# 4V Drive Pch MOSFET

## RRH100P03

### ●Structure

Silicon P-channel MOSFET

### ●Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

### ●Application

Switching

### ●Packaging specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RRH100P03		○

### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DS}$	-30	V	
Gate-source voltage	$V_{GS}$	±20	V	
Drain current	Continuous	$I_D$	±10	A
	Pulsed	$I_{DP}^{*1}$	±40	A
Source current (Body Diode)	Continuous	$I_S$	-1.6	A
	Pulsed	$I_{SP}^{*1}$	-40	A
Power dissipation	$P_D^{*2}$	2.0	W	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

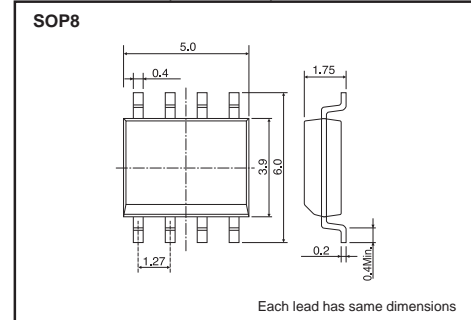
\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$   
\*2 Mounted on a ceramic board.

### ●Thermal resistance

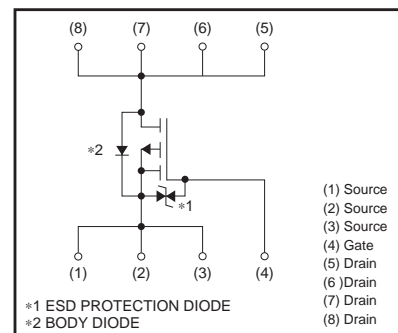
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)^*$	62.5	°C / W

\* Mounted on a ceramic board.

### ●Dimensions (Unit : mm)



### ●Inner circuit



## ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I <sub>GSS</sub>	–	–	±10	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	–30	–	–	V	I <sub>D</sub> =–1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	–	–	–1	μA	V <sub>DS</sub> =–30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS(th)</sub>	–1.0	–	–2.5	V	V <sub>DS</sub> =–10V, I <sub>D</sub> =–1mA
Static drain-source on-state resistance	R <sub>DS(on)</sub> *	–	9.0	12.6	mΩ	I <sub>D</sub> =–10A, V <sub>GS</sub> =–10V
		–	12.5	17.5		I <sub>D</sub> =–5A, V <sub>GS</sub> =–4.5V
		–	14.0	19.6		I <sub>D</sub> =–5A, V <sub>GS</sub> =–4.0V
Forward transfer admittance	Y <sub>fs</sub>  *	13	–	–	S	I <sub>D</sub> =–10A, V <sub>DS</sub> =–10V
Input capacitance	C <sub>iss</sub>	–	3600	–	pF	V <sub>DS</sub> =–10V
Output capacitance	C <sub>oss</sub>	–	450	–	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>riss</sub>	–	450	–	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	–	25	–	ns	I <sub>D</sub> =–5A, V <sub>DD</sub> ≒ –15V
Rise time	t <sub>r</sub> *	–	60	–	ns	V <sub>GS</sub> =–10V
Turn-off delay time	t <sub>d(off)</sub> *	–	150	–	ns	R <sub>L</sub> =3.0Ω
Fall time	t <sub>f</sub> *	–	100	–	ns	R <sub>G</sub> =10Ω
Total gate charge	Q <sub>g</sub> *	–	39	–	nC	I <sub>D</sub> =–10A, V <sub>DD</sub> ≒ –15V
Gate-source charge	Q <sub>gs</sub> *	–	8.5	–	nC	V <sub>GS</sub> =–5V
Gate-drain charge	Q <sub>gd</sub> *	–	13.5	–	nC	R <sub>L</sub> =1.5Ω R <sub>G</sub> =10Ω

\*Pulsed

## ●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V <sub>SD</sub> *	–	–	–1.2	V	I <sub>S</sub> =–10A, V <sub>GS</sub> =0V

\*Pulsed

●Electrical characteristics curves

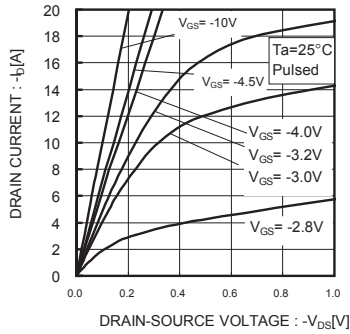


Fig.1 Typical output characteristic(I)

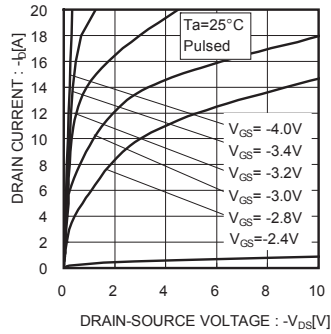


Fig.2 Typical output characteristics(II)

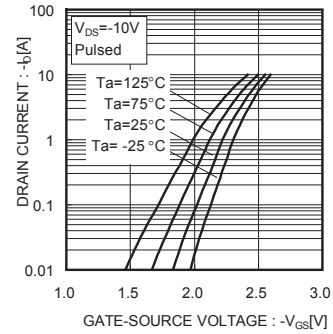


Fig.3 Typical Transfer Characteristics

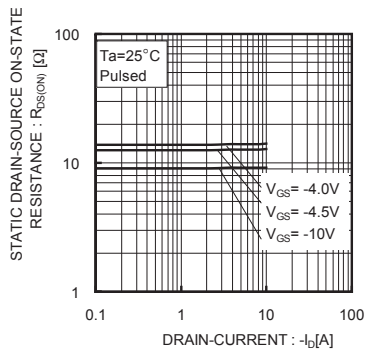


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

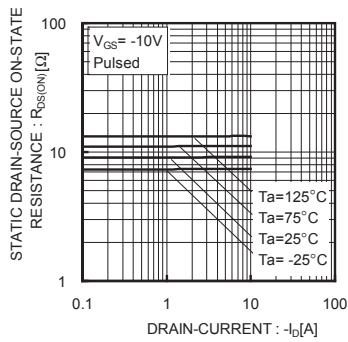


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

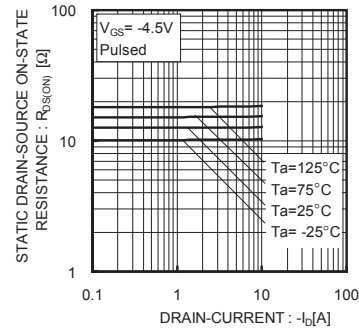


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

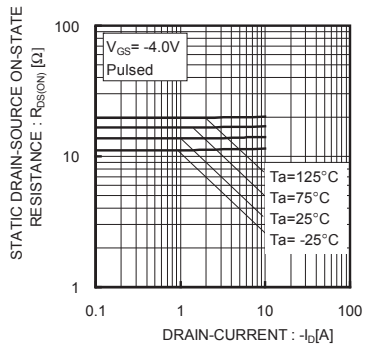


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

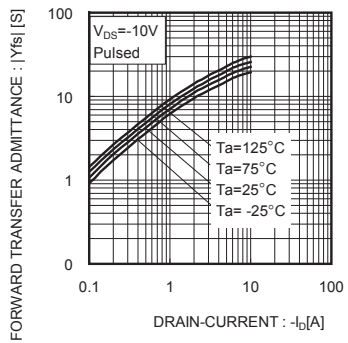


Fig.8 Forward Transfer Admittance vs. Drain Current

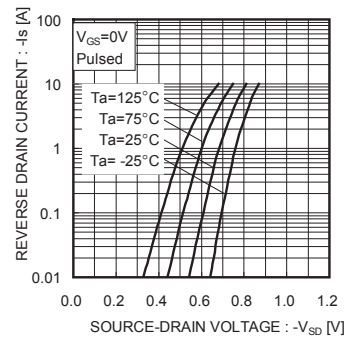


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

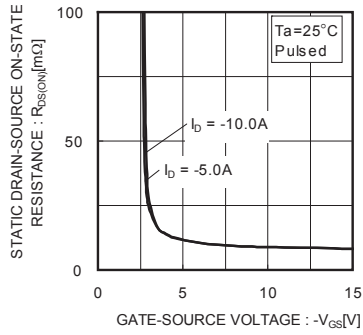


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

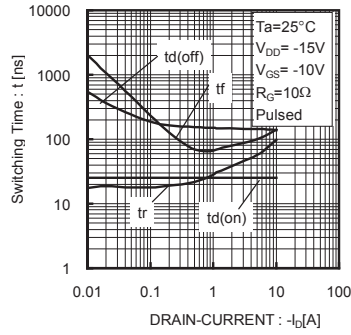


Fig.11 Switching Characteristics

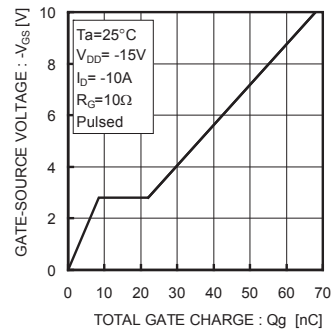


Fig.12 Dynamic Input Characteristics

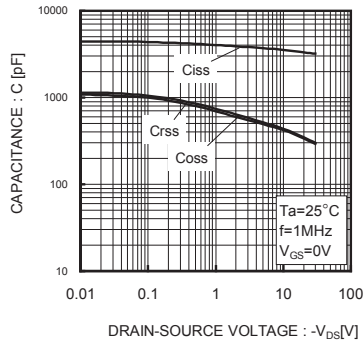


Fig.13 Typical Capacitance vs. Drain-Source Voltage

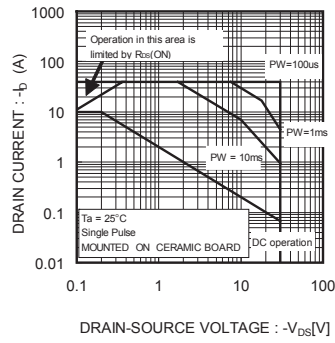


Fig.14 Maximum Safe Operating Area

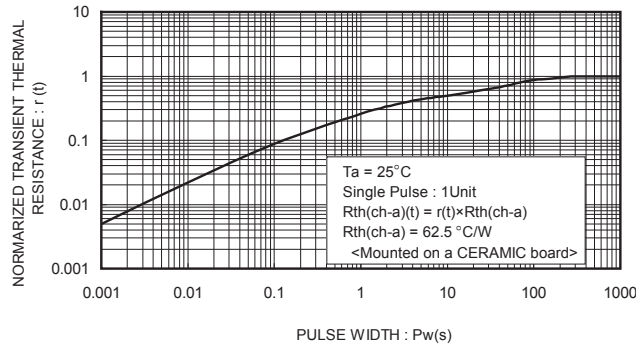


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

●Measurement circuit

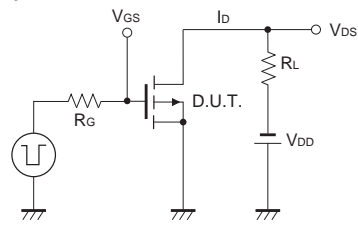


Fig.1-1 Switching Time Measurement Circuit

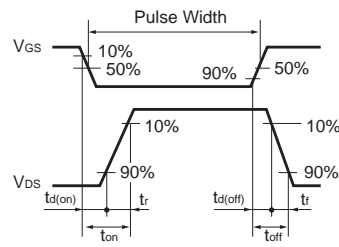


Fig.1-2 Switching Waveforms

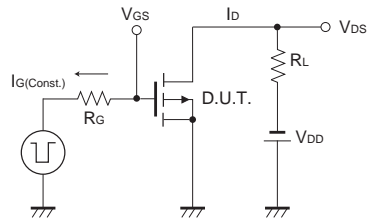


Fig.2-1 Gate Charge Measurement Circuit

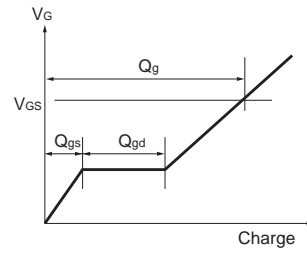


Fig.2-2 Gate Charge Waveform

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